



A -240dB-FOM and -115dBc/Hz-100kHz-PN, 7.7GHz-Ring-DCO-Based Digital PLL Using P/I-Gain Co-Optimization

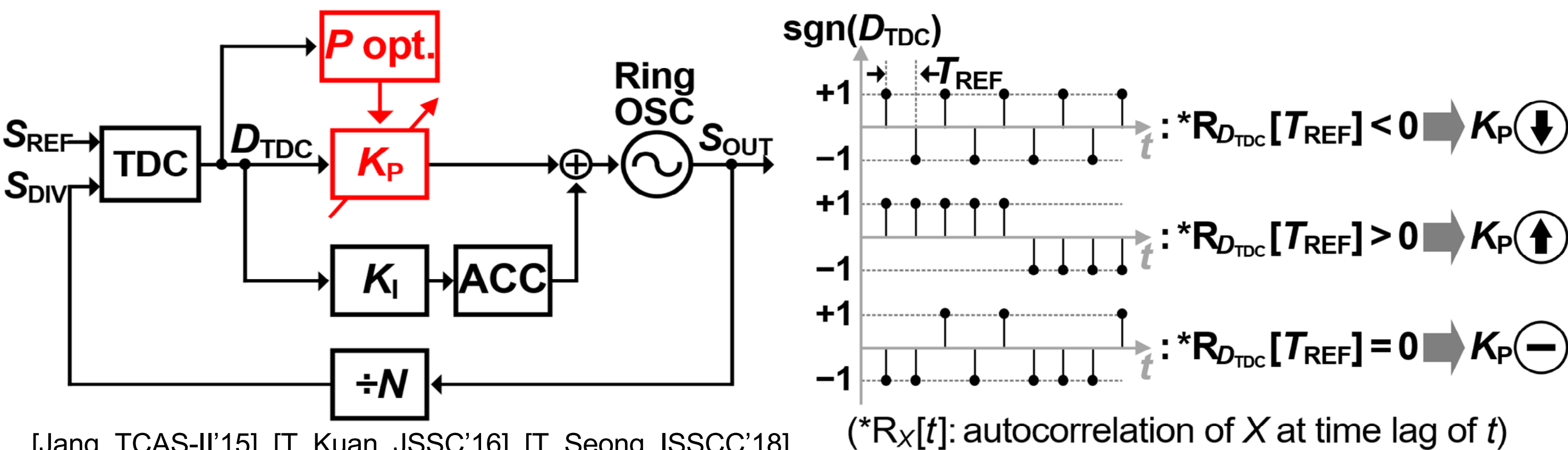
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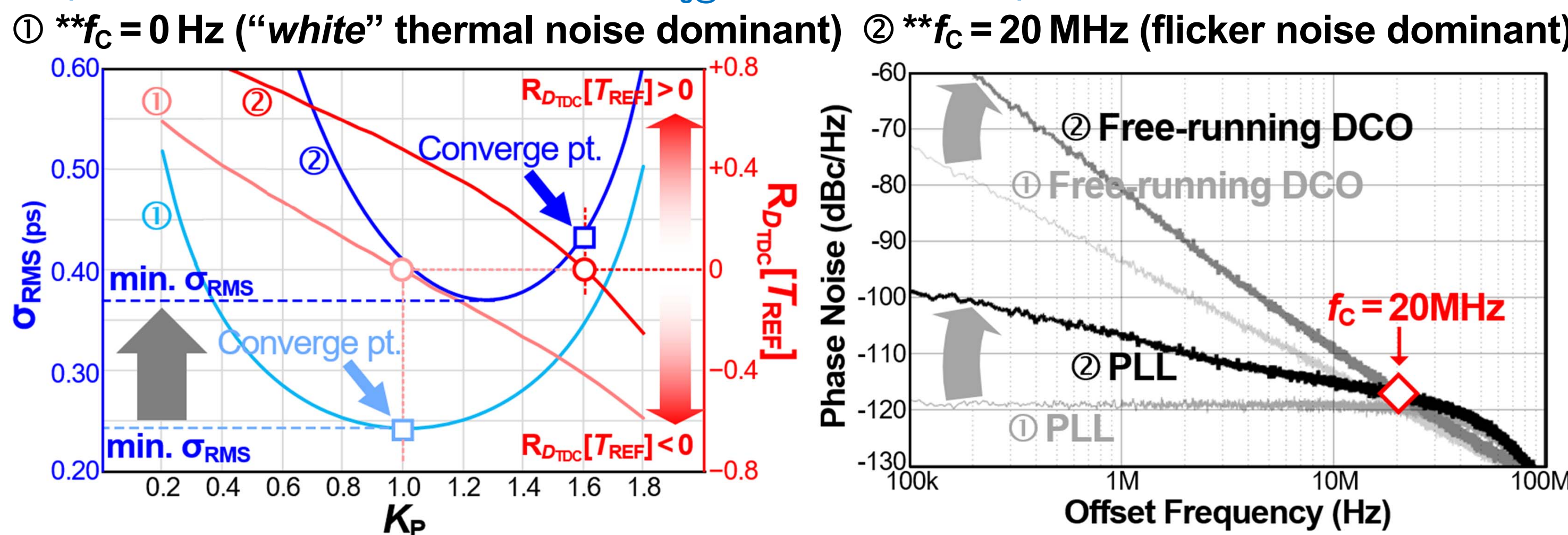
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Introduction

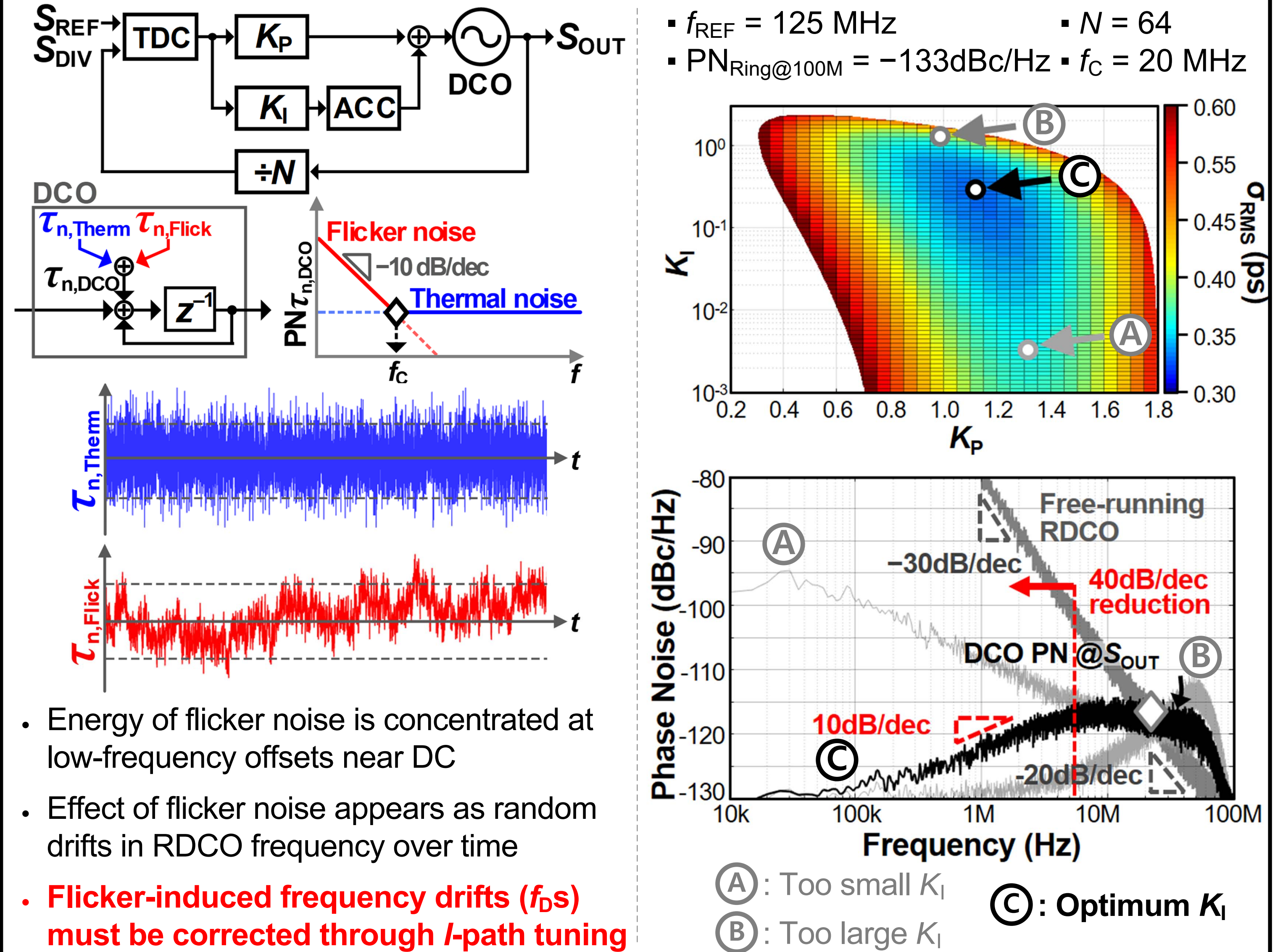
Conventional Ring-Oscillator-Based Digital PLLs – P-path gain (K_P) optimization based on $R_{D_{TDC}}[T_{REF}]$



Simulated RMS jitter (σ_{RMS}) and phase noise ($f_{REF} = 125$ MHz, $N = 64$, $K_I = 2^8$, $PN_{Ring@100M} = -133$ dBc/Hz) (** f_c : flicker corner frequency)

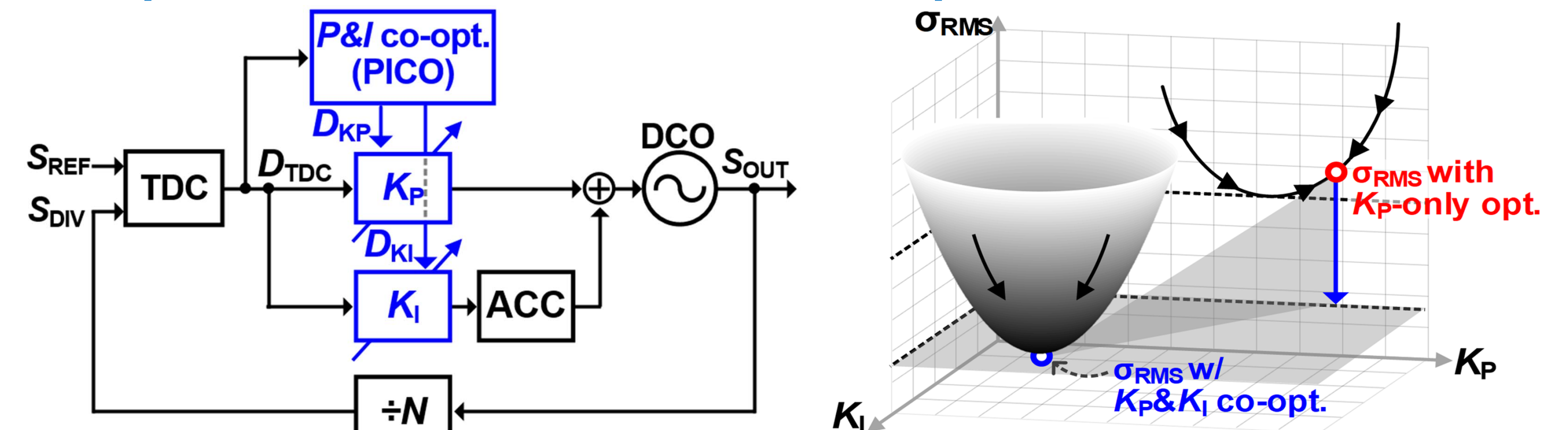


Effect of Flicker Noise



Proposed P- & I-Gain Co-Optimization (PICO)

Proposed Jitter Minimization Technique

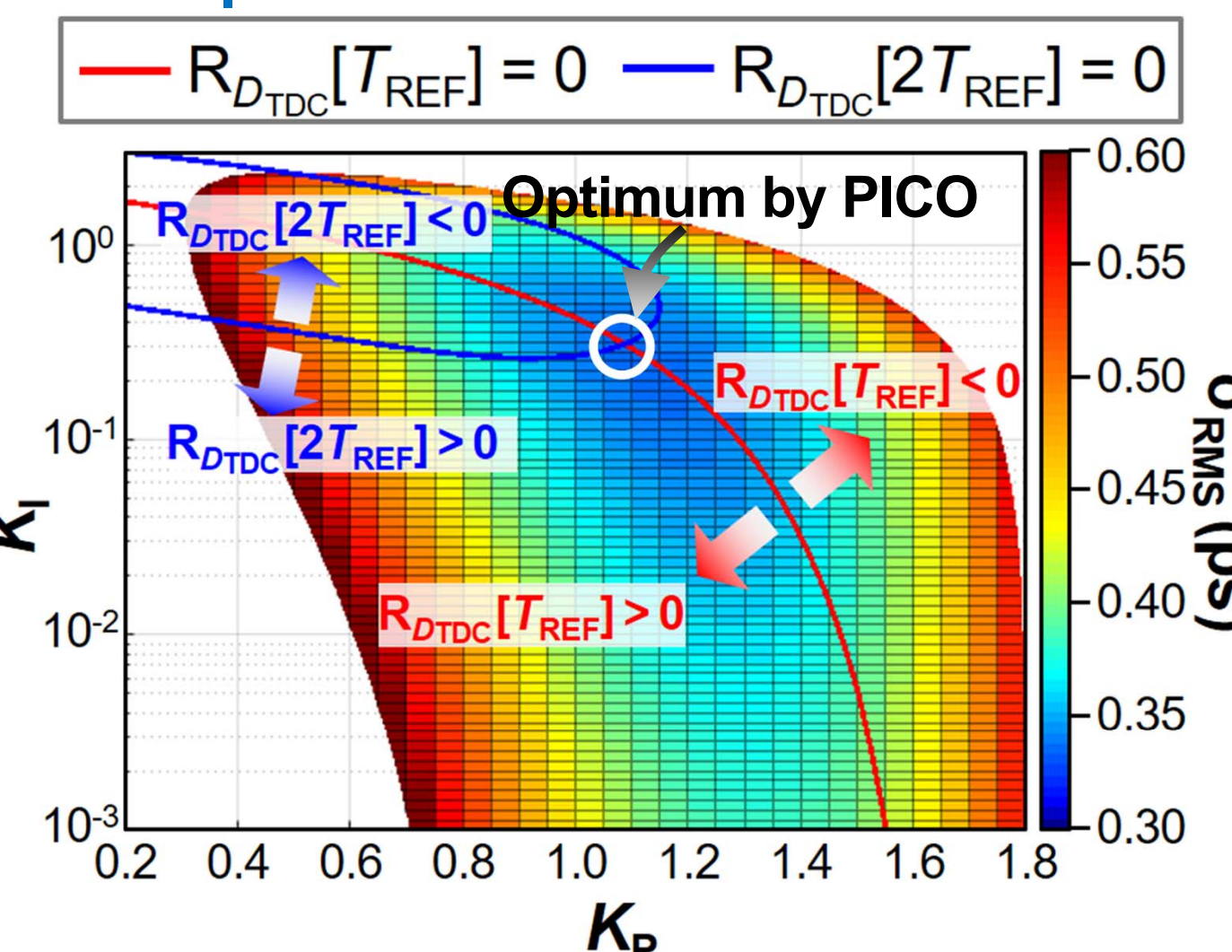


Principles & Implementation of PICO

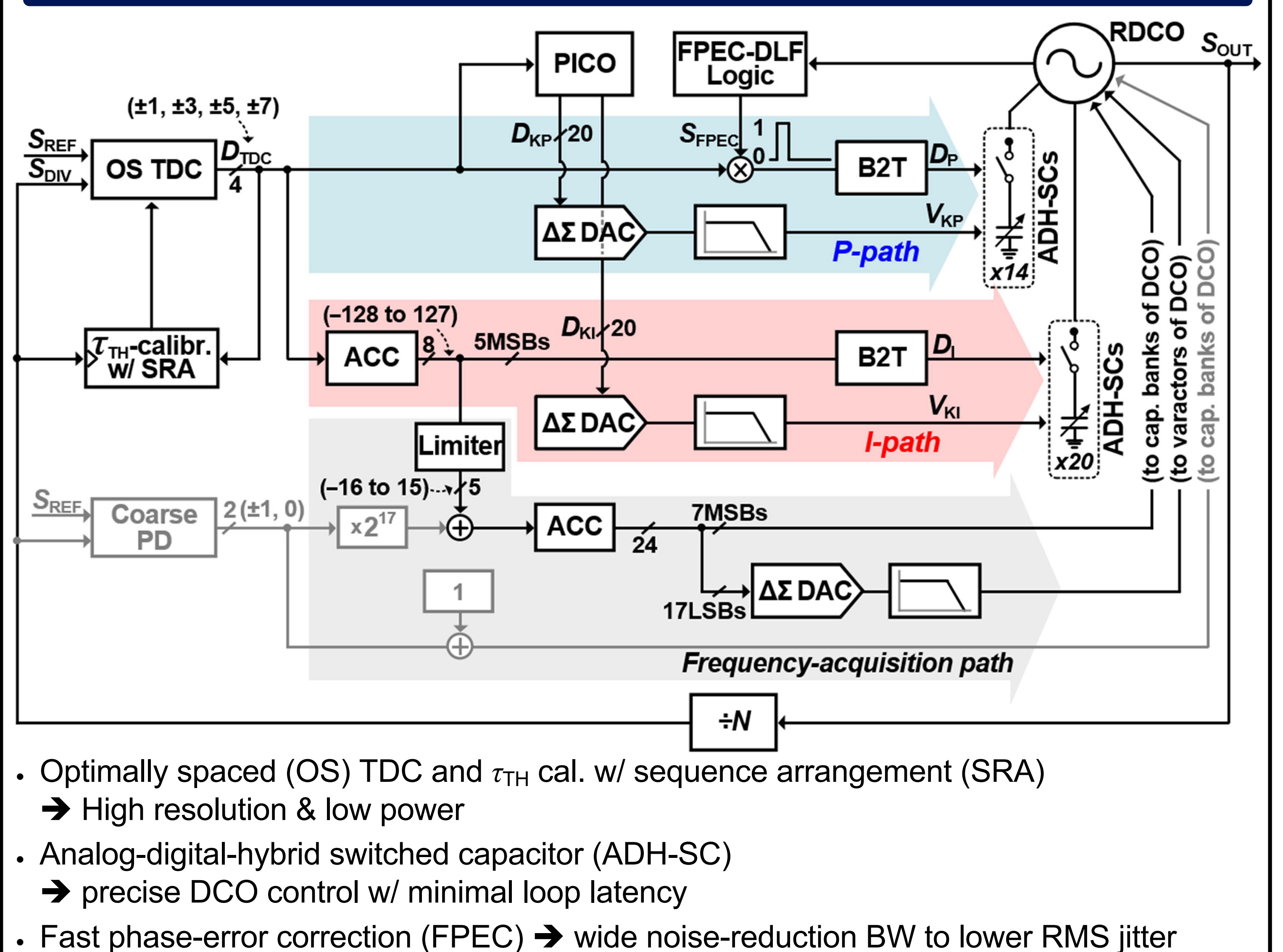
- Principles of PICO
 - ① Cross-correlation btw $\tau_{ERR}[n]$ and $\tau_{ERR}[n+1]$ is zero
 $\rightarrow E[\tau_{ERR}[n] \cdot \tau_{ERR}[n+1]] = R_{TERR}[T_{REF}] = 0$
 $(R_{TERR}[T_{REF}] = \text{autocorrelation of } \tau_{ERR} @ T_{REF})$
 - ② Cross-correlation btw $\Delta f_D[n]$ and $\tau_{ERR}[n+1]$ is zero
 $\rightarrow E[\Delta f_D[n] \cdot \tau_{ERR}[n+1]] = 0$, $\Delta f_D[n] \propto (\tau_{ERR}[n] - \tau_{ERR}[n-1])$
 $\rightarrow R_{TERR}[T_{REF}] - R_{TERR}[2T_{REF}] = 0$

- Implementation of PICO
 - P-path: $R_{D_{TDC}}[T_{REF}] \rightarrow 0$ $D_{TDC} \rightarrow [z^{-1}] \rightarrow [ACC] \rightarrow D_{KP}$
 - I-path: $R_{D_{TDC}}[2T_{REF}] \rightarrow 0$ $D_{TDC} \rightarrow [z^{-2}] \rightarrow [ACC] \rightarrow D_{KI}$

Verification: Optimal K_P & K_I from Behavioral Sim.

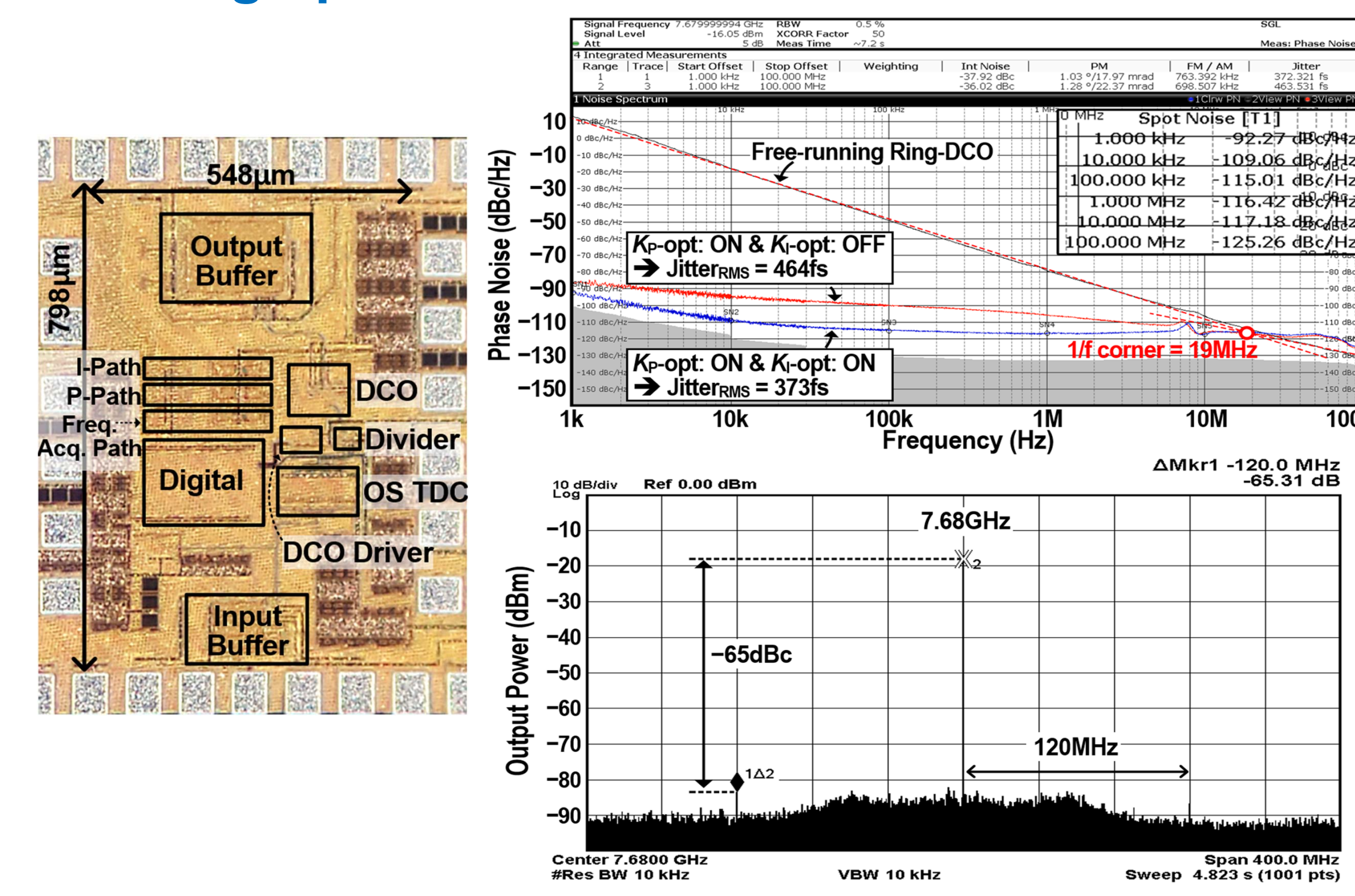


Overall Architecture

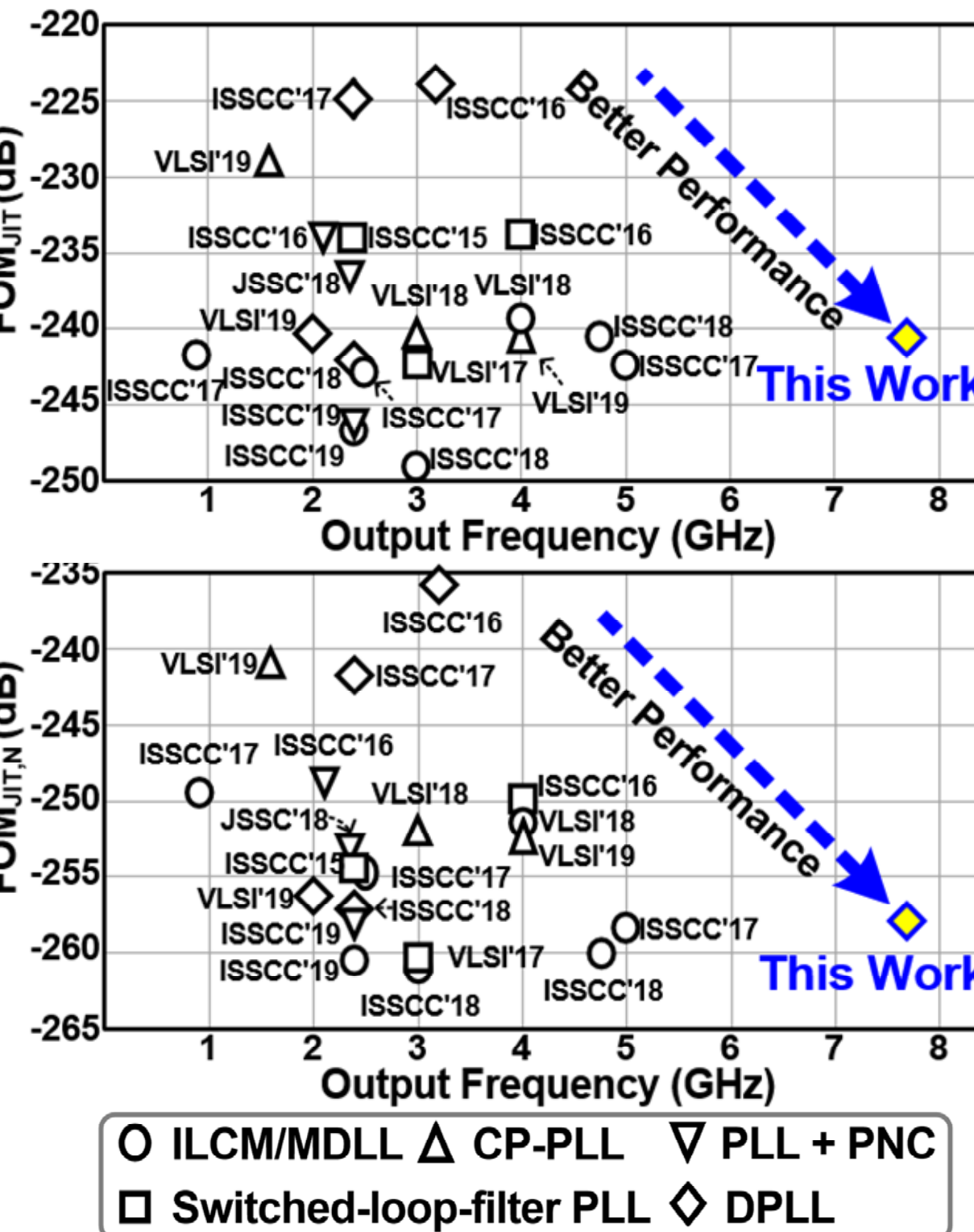


Measurement Results

Micrograph and Measurement Results



Performance Summary



Reference	This Work	ISSCC'19 X. Yang	ISSCC'18 T. Seong	ISSCC'18 K. M. Megawar	ISSCC'17 D. Coombs	JSSC'18 S.-S. Nagam
Architecture	DPLL	SSPLL + PNC	DPLL	ILCM	ILCM	SSPLL + PNC
Technology	65nm	28nm	65nm	65nm	65nm	65nm
Area (mm ²)	0.075	0.023	0.055	0.16	0.09	0.022
f_{REF} (MHz)	120	150	75	54	125	49.15
f_{OUT} (GHz)	7.68	2.4	2.4	4.752	5	2.36
Multi. factor (N)	64	24	32	88	40	48
100kHz PN (dBc/Hz)*	-132.7	-128.9	-124.6	-123.3	-124.0	-128.5
1MHz PN (dBc/Hz)*	-134.1	-133.0	-127.4	-127.2	-129.9	-126.6
Jitter _{RMS} (fs)	373 (1k to 100M)	248 (10k to 100M)	320 (1k to 100M)	366 (1k to 100M)	340 (10k to 40M)	630 (1k to 100M)
Power (mW)	6.48	4.1	6.0	6.5	5.3	5.86
FoM _{JIT} (dB)**	-240.5	-246.0	-242.1	-240.6	-242.4	-236.3
FoM _{JIT,N} (dB)***	-258.5	-259.8	-257.2	-260.0	-258.4	-253.1
Spur (dBc)	-65	-63	-75	-53	-45	-55

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